FAIRCHILD SEMICONDUCTOR®

December 2013

FDH44N50

N-Channel SMPS Power MOSFET

500 V, 44 A, 120 mΩ

Features

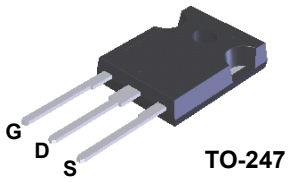
- Low Gate Charge Q_g Results in Simple Drive Requirement (Typ. 90 nC)
- Improved Gate, Avalanche and High Reapplied dv/dt Ruggedness
- Reduced $R_{DS(on)}$ (110 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 22 A)
- Reduced Miller Capacitance and Low Input Capacitance (Typ. C_{rss} = 40 pF)
- Improved Switching Speed with Low EMI
- 175°C Rated Junction Temperature

Description

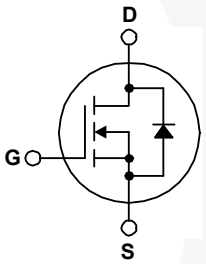
UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

Applications

- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply



TO-247



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted.

Symbol	Parameter	FDH44N50	Unit
V_{DSS}	Drain to Source Voltage	500	V
V_{GS}	Gate to Source Voltage	±30	V
I_D	Drain Current		
	Continuous (T_C = 25°C, V_{GS} = 10 V)	44	A
	Continuous (T_C = 100°C, V_{GS} = 10 V)	32	A
	Pulsed[1]	176	A
P_D	Power Dissipation	750	W
	Derate Above 25°C	5	W/°C
T_J, T_{STG}	Operating and Storage Temperature	-55 to 175	°C
	Soldering Temperature for 10 Seconds	300 (1.6mm from case)	°C
	Mounting Torque, 8-32 or M3 Screw	10ibf*in (1.1N*m)	

Thermal Characteristics

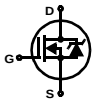
Symbol	Parameter	FDH44N50	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDH44N50	FDH44N50	TO-247	Tube	N/A	N/A	30 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
Statics							
B_{VDSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V		500	-	-	V
ΔB_{VDSS} / ΔT_J	Breakdown Voltage Temp. Coefficient	Reference to 25°C, I_D = 1 mA		-	0.61	-	V/°C
$r_{DS(ON)}$	Drain to Source On-Resistance	V_{GS} = 10 V, I_D = 22 A		-	0.11	0.12	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA		2	3.15	4	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 500 V, V_{GS} = 0 V	T_C = 25°C	-	-	25	μA
			T_C = 150°C	-	-	250	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V		-	-	±100	nA
Dynamics							
g_{fs}	Forward Transconductance	V_{DS} = 50 V, I_D = 22 A		11	-	-	S
$Q_{g(TOT)}$	Total Gate Charge at 10V	V_{GS} = 10 V, V_{DS} = 400 V, I_D = 44 A		-	90	108	nC
Q_{gs}	Gate to Source Gate Charge			-	24	29	nC
Q_{gd}	Gate to Drain “Miller” Charge			-	31	37	nC
$t_{d(ON)}$	Turn-On Delay Time	V_{DD} = 250 V, I_D = 44 A, R_G = 2.15 Ω, R_D = 5.68 Ω		-	16	-	ns
t_r	Rise Time			-	84	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time			-	45	-	ns
t_f	Fall Time			-	79	-	ns
C_{ISS}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0 V, f = 1 MHz		-	5335	-	pF
C_{OSS}	Output Capacitance			-	645	-	pF
C_{RSS}	Reverse Transfer Capacitance			-	40	-	pF
Avalanche Characteristics							
E_{AS}	Single Pulse Avalanche Energy[2]			1500	-	-	mJ
I_{AR}	Avalanche Current			-	-	44	A
Drain-Source Diode Characteristics							
I_S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode. 		-	-	44	A
I_{SM}	Pulsed Source Current[1] (Body Diode)			-	-	176	A
V_{SD}	Source to Drain Diode Voltage	I_{SD} = 44 A		-	0.900	1.2	V
t_{rr}	Reverse Recovery Time	I_{SD} = 44 A, dI_{SD}/dt = 100 A/μs		-	920	1100	ns
Q_{RR}	Reverse Recovered Charge	I_{SD} = 44 A, dI_{SD}/dt = 100 A/μs		-	14	18	μC

Notes:
1: Repetitive rating; pulse-width limited by maximum junction temperature.
2: Starting T_J = 25°C, L = 1.61 mH, I_{AS} = 44 A

Typical Characteristics

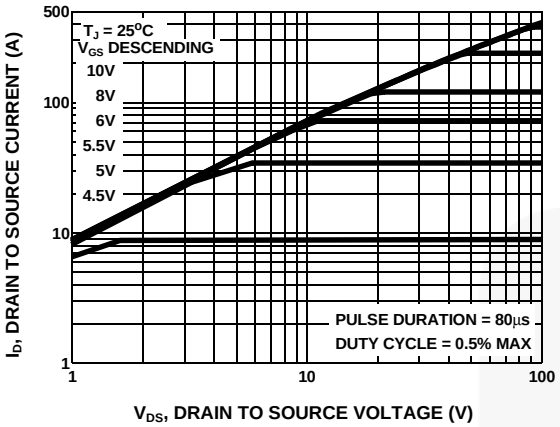


Figure 1. Output Characteristics

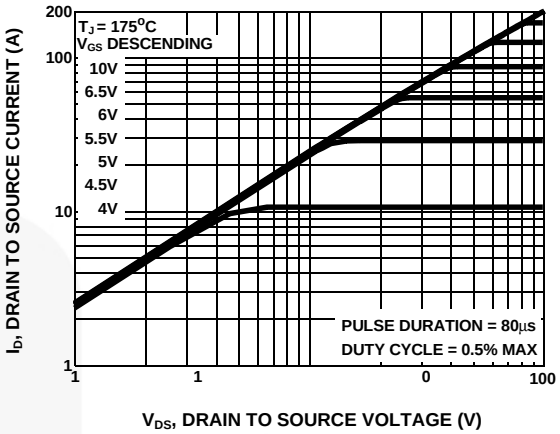


Figure 2. Output Characteristics

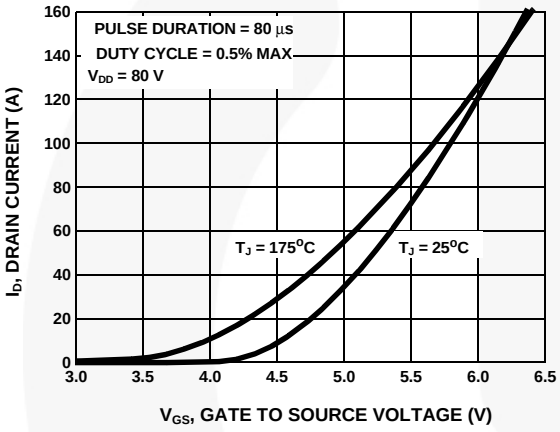


Figure 3. Transfer Characteristics

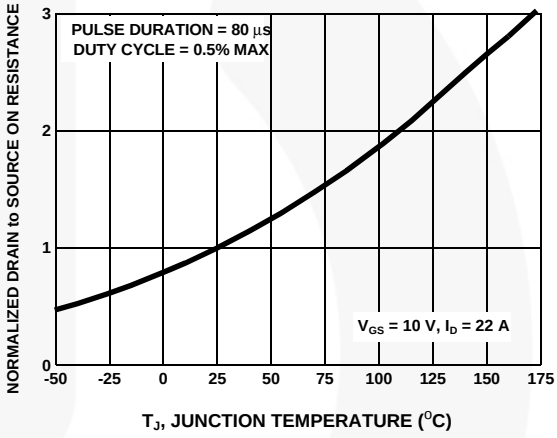


Figure 4. Normalized Drain To Source On Resistance vs Junction Temperatrue

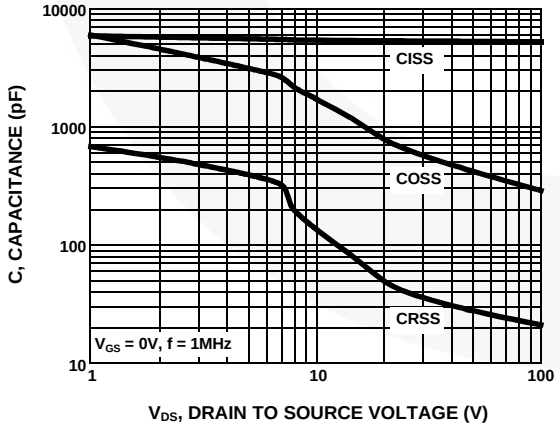


Figure 5. Capacitance vs Drain To Source Voltage

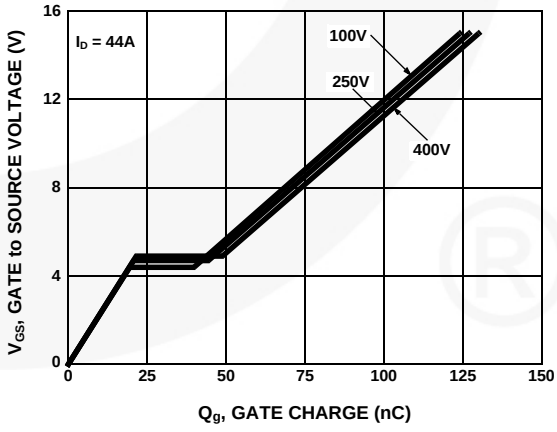


Figure 6. Gate Charge Waveforms For Constant Gate Current

Typical Characteristics (Continued)

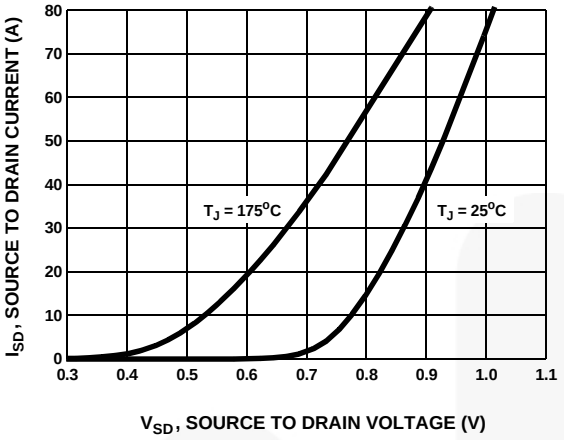


Figure 7. Body Diode Forward Voltage vs Body Diode Current

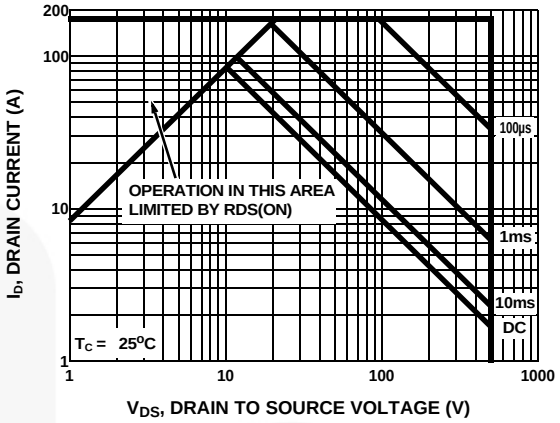


Figure 8. Maximum Safe Operating Area

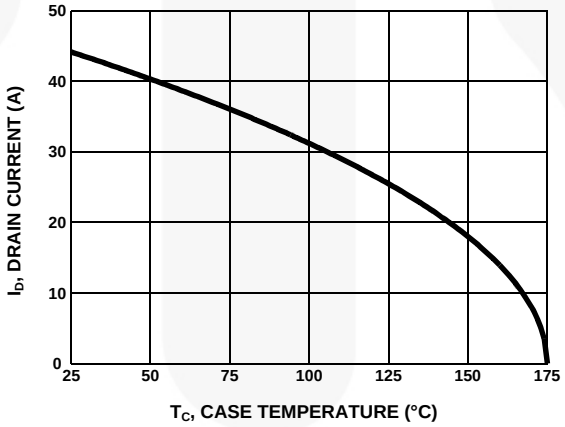


Figure 9. Maximum Drain Current vs Case Temperature

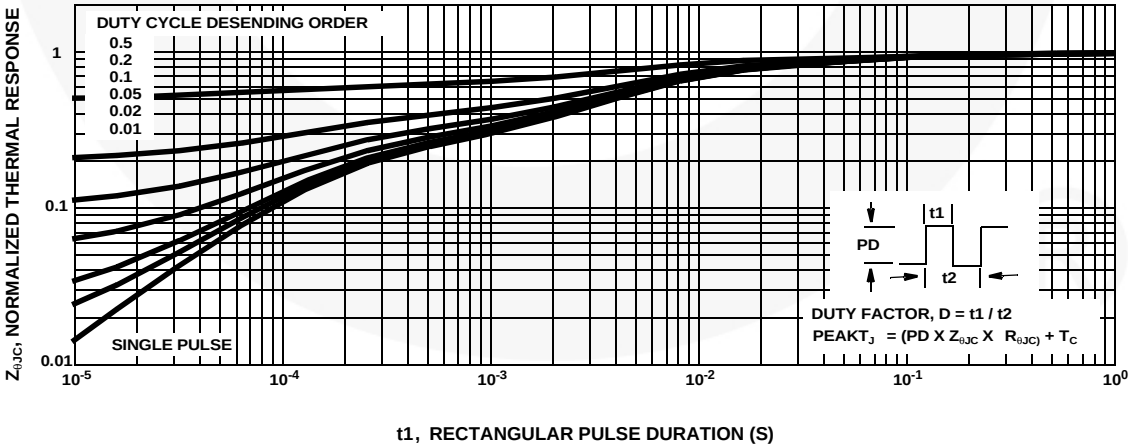


Figure 10. Normalized Transient Thermal Impedance, Junction to Case

Test Circuits and Waveforms

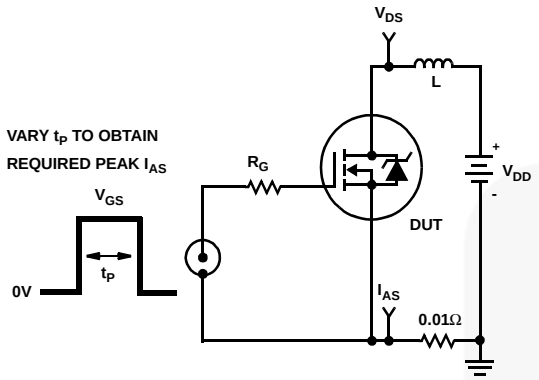


Figure 11. Unclamped Energy Test Circuit

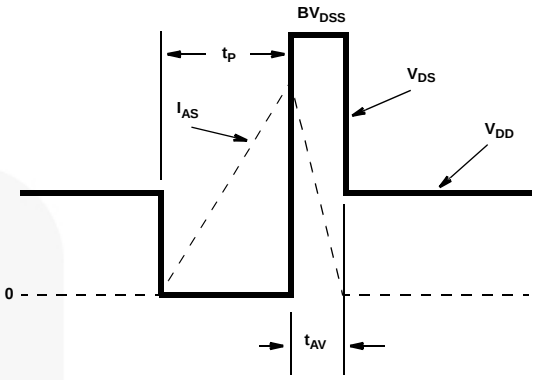


Figure 12. Unclamped Energy Waveforms

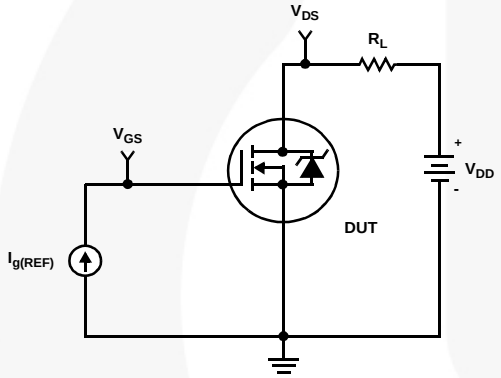


Figure 13. Gate Charge Test Circuit

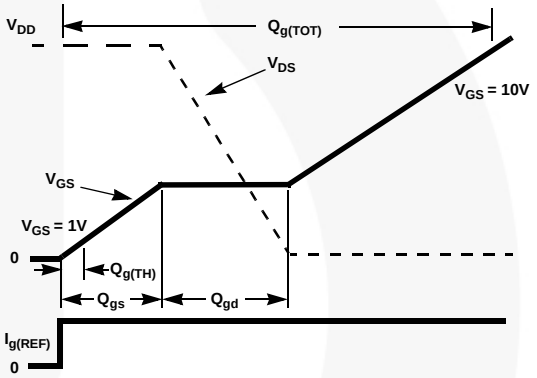


Figure 14. Gate Charge Waveforms

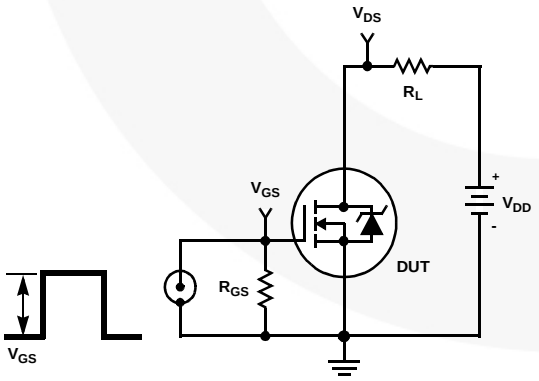


Figure 15. Switching Time Test Circuit

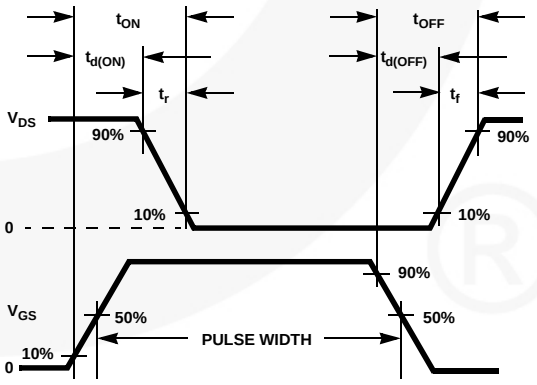
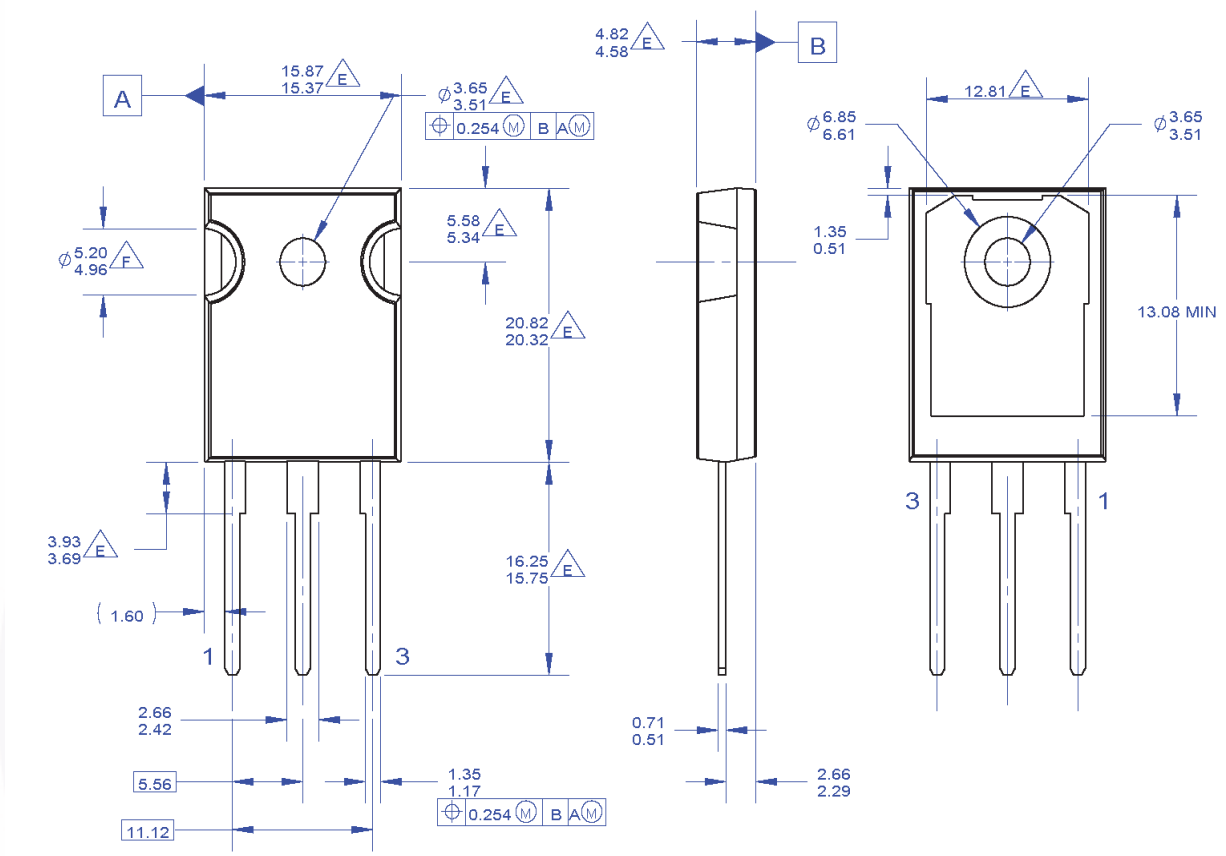


Figure 16. Switching Time Waveform

Mechanical Dimensions



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F NOTCH MAY BE SQUARE

G. DRAWING FILENAME: MKT-TO247A03_REV03

Figure 17. TO-247, Molded, 3-Lead, Jedec Variation AB

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